



04-16-02
0410

0300

3808
48/9
2-2603

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

	U.S. Patent Application 09/944823)	PATENT
)	
German Title:	Halbleiterlaserchip und Verfahren zum Herstellen eines Halbleiterlaserchips)	
)	
English Translation:	Semiconductor laser chip and method for fabricating a semiconductor laser chip)	
)	
Applicant:	Infineon Technologies, AG)	
)	
Inventors:	Bernd Borchert)	
)	
Attorney Docket:	32226.12)	

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir:

PRELIMINARY AMENDMENT

In the above-entitled patent application, please amend the application as follows:

In the Claims

1 1. (amended) Semiconductor laser chip having a semiconductor laser element
2 and a beam shaper integrated into the semiconductor laser chip and serving to shape a laser
3 beam emitted by the semiconductor laser element, the beam shaper being arranged in a
4 manner integrated in the semiconductor laser element in the exit direction of a laser beam
5 emitted by the semiconductor laser element, such that the emitted laser beam is guided
6 through the beam shaper, the beam shaper having a predetermined concentration profile of
7 oxidized aluminium.

1 3. (amended) Semiconductor laser chip according to Claim 1, in which the beam
2 shaper has aluminium-containing material.